

METHOD FOR FORMING CONDUCTIVE INTERCONNECTION STRUCTURE

ABSTRACT

Embodiments of the present disclosure provide a method for forming a
5 conductive interconnect structure, including: forming a predetermined mask pattern on
a conductive layer; doping a first mask pattern to form a doped region having a
predetermined depth in the first mask pattern, where the first mask pattern is the
predetermined mask pattern that has been doped, and a second mask pattern is the
predetermined mask pattern that is undoped; where the doped region has a higher etch
10 rate than an undoped region; and etching the conductive layer by the first mask pattern
and the second mask pattern to form the conductive interconnect structure; and where
a conductive line in a region corresponding to the second mask pattern has a greater
height than a conductive line in a region corresponding to the first mask pattern, and
the conductive line in the region corresponding to the second mask pattern is formed
15 as a conductive via.

Fig. 4